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Supporting Information

Synthesis of InAl-alloyed Ga_2O_3 nanowires for self-powered ultraviolet detectors by CVD method

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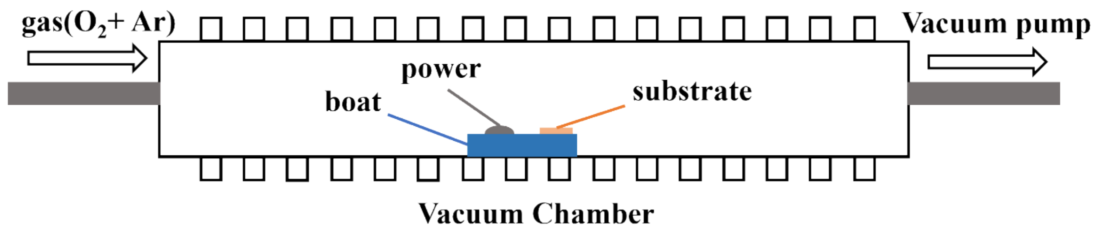

Fig S1. Schematic diagram of CVD experimental device.

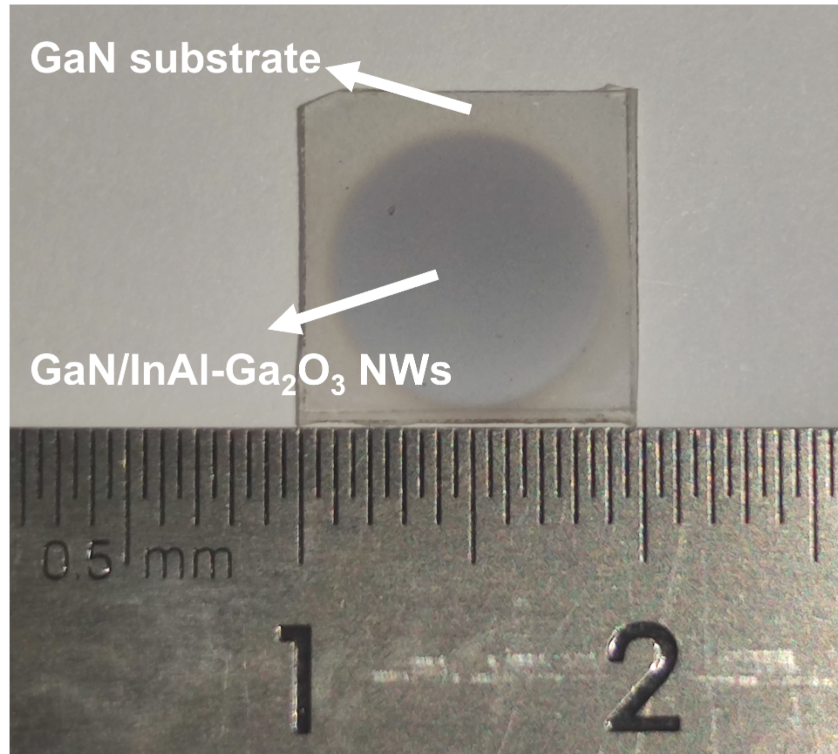

Fig S2 . Physical image of the synthesized GaN/InAl-Ga2O3 NWs p-n junction.

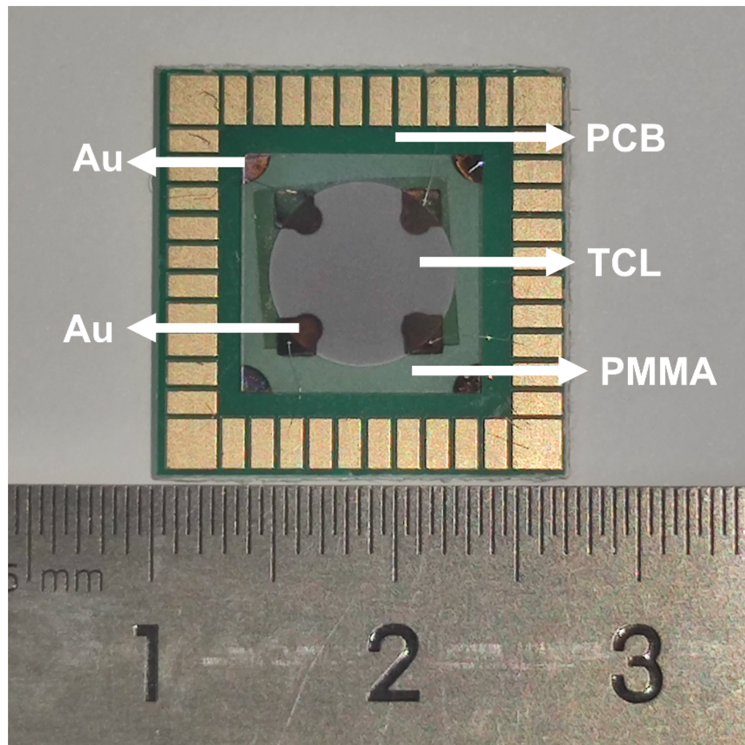

Fig S3. Image of prepared GaN/InAl-Ga2O3NWs photodetector device.

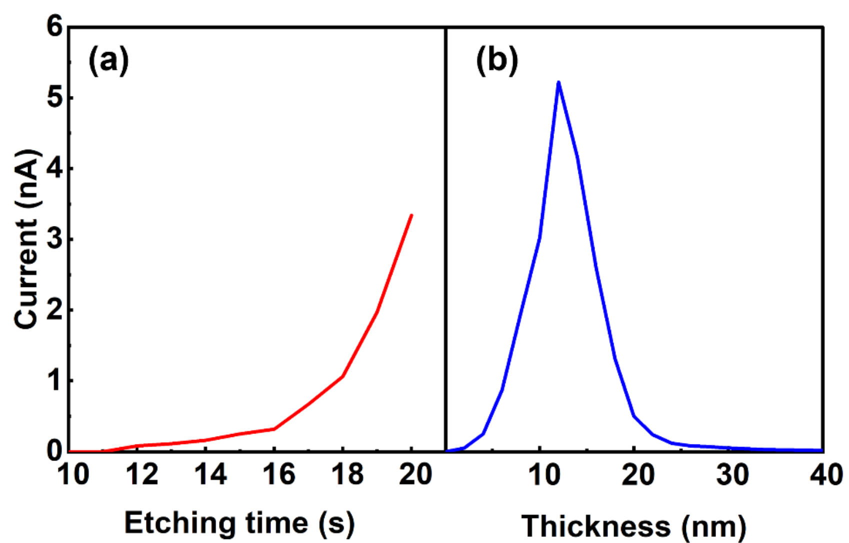

Fig S4. (a) Effect of etching time on photocurrent. (b) Effect of transparent conductive layer Au film thickness on photocurrent.

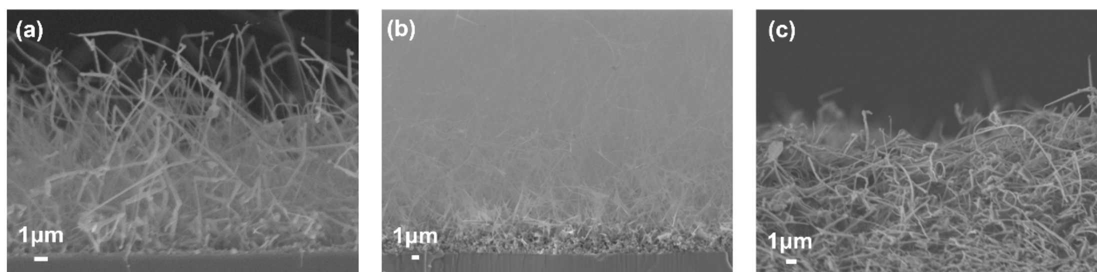

Fig S5. Cross-sections of GaN/InAl-Ga2O3NWs after different reaction times: (a) 3 min; (b) 5 min; (c) 10 min.